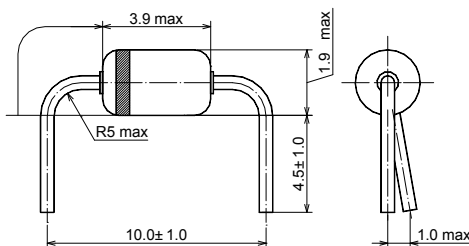
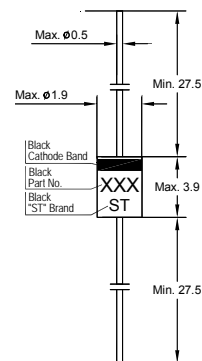


## Silicon Schottky Barrier Diode

Characteristics equivalent to  
1N60P and 1N60S



**Glass case DO-35-1**  
Dimensions in mm



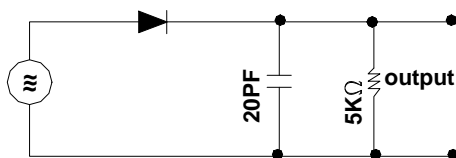
**Glass Case DO-35**  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	45	V
Reverse Voltage	$V_R$	20	V
Average Rectified Output Current	$I_O$	50	mA
Peak Forward Current	$I_{FM}$	150	mA
Surge Forward Current	$I_{surge}$	500	mA
Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	- 55 to + 175	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1\text{ V}$	$I_F$	4	-	mA
Reverse Current at $V_R = 10\text{ V}$	$I_R$	-	50	$\mu\text{A}$
	ST60P	-	100	
	ST60S	-		
Rectification efficiency at $V_i = 2\text{ Vrms}$ , $R = 5\text{ K}\Omega$ , $C = 20\text{ pF}$ , $f = 40\text{ MHz}$	$\eta$	55	-	%



Input 2Vrms

Rectification Efficiency Measurement Circuit